

SOD-123 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SOD-123



■Maximum Rating 最大额定值

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B5817W -6AF	B5818W -6AF	B5819W -6AF	Unit 单位
Device Marking 产品印字		SJ	SK	SL	
Peak Reverse Voltage 反向峰值电压	V _{RRM}	20	30	40	V
DC Reverse Voltage 直流反向电压	V _R	20	30	40	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	14	21	28	V
Forward Rectified Current 正向整流电流	I _F	1			A
Peak Surge Current 峰值浪涌电流	I _{FSM}	25			A
Repetitive Peak Surge Current 重复峰值浪涌电流	I _{FRM}	3			A
Power Dissipation 耗散功率	P _D	250			mW
Thermal Resistance J-A 结到环境热阻	R _{θJA}	400			°C/W
Junction Temperature 结温	T _J	-65to+125			°C
Storage Temperature 储藏温度	T _{stg}	-65to+150			°C

■Electrical Characteristics 电特性

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	B5817W -6AF	B5818W -6AF	B5819W -6AF	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V _R	20	30	40	V	I _R =1mA
Forward Voltage 正向电压	V _F	0.45 0.75	0.55 0.875	0.6 0.9	V	I _F =1A I _F =3A
Reverse Current 反向电流	I _R	0.05 (T _a =25°C) 8 (T _a =100°C)			mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _T	30			pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

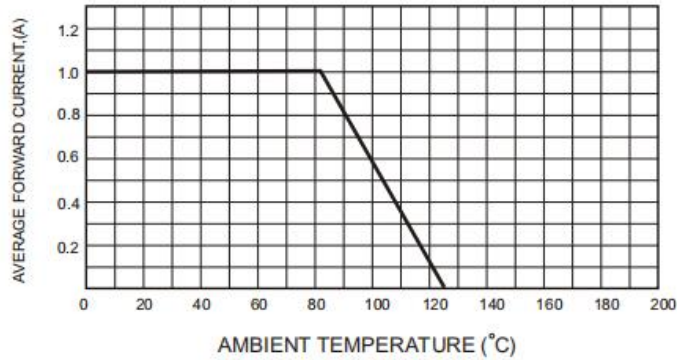


FIG.3 - Power Derating Curve

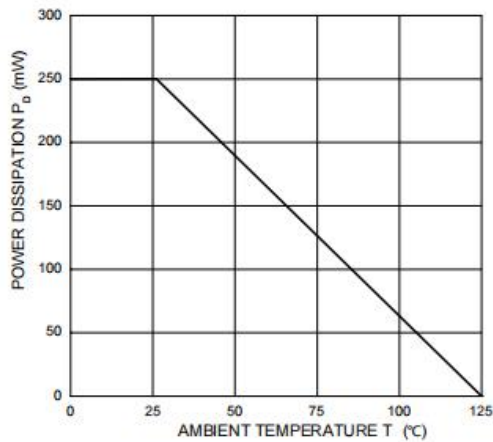


FIG.4-TYPICAL JUNCTION CAPACITANCE

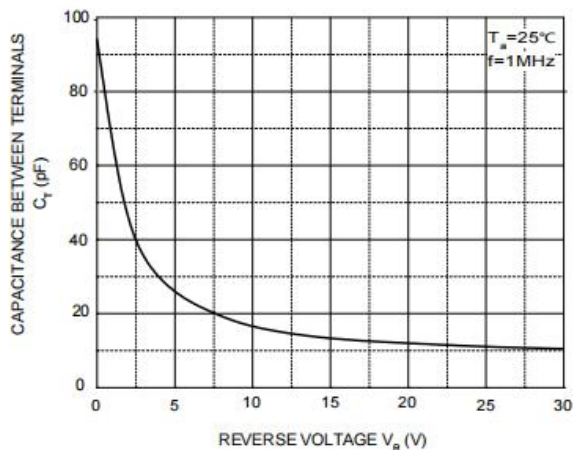


FIG.2-TYPICAL FORWARD

CHARACTERISTICS

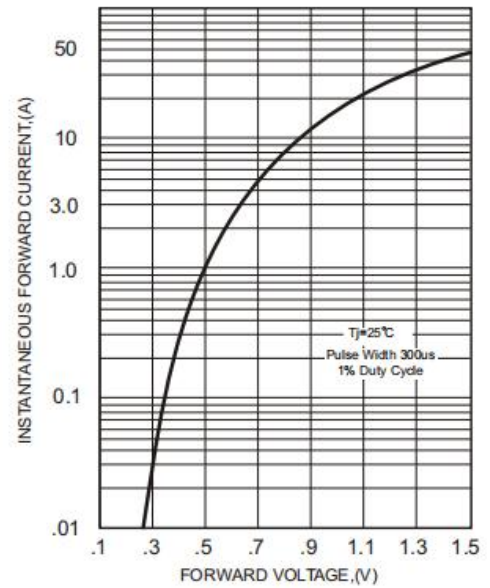
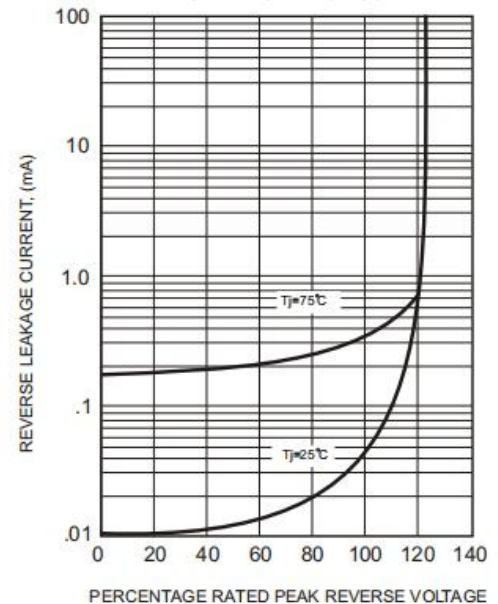
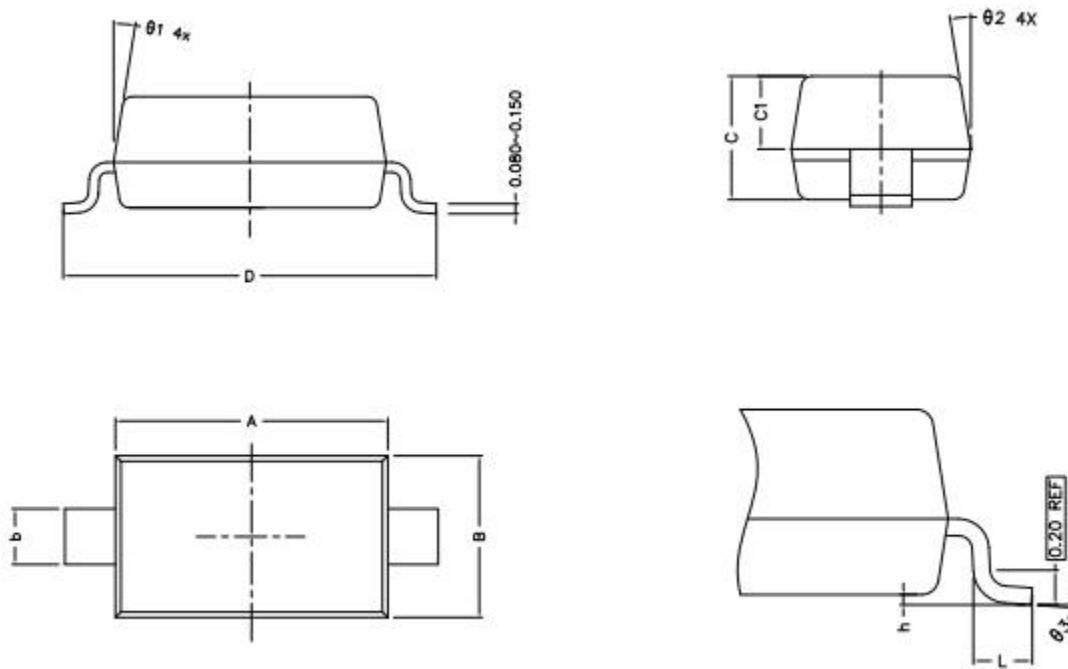


FIG.5 - TYPICAL REVERSE

CHARACTERISTICS



■ Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.600	2.800	0.102	0.110
B	1.500	1.700	0.059	0.067
C	1.050	1.150	0.041	0.045
C1	0.600	0.700	0.024	0.028
D	3.550	3.850	0.140	0.152
L	0.250	0.450	0.010	0.018
b	0.450	0.650	0.018	0.026
h	0.020	0.120	0.001	0.005
θ 3	0°	7°	0°	7°